2SK2899-01R

FUJI POWER MOSFET

Fuji Electric

200509

N-CHANNEL SILICON POWER MOSFET

FAP-IIIB SERIES

■ Features

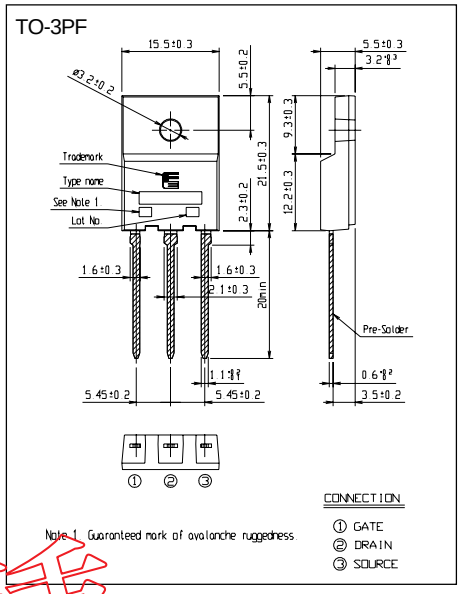
- High speed switching
- Low on-resistance
- No secondary breakdown
- Low driving power
- High voltage
- Avalanche-proof

■ Applications

- Switching regulators
- DC-DC converters
- General purpose power amplifier

■ Outline Drawings

TO-3PF



■ Maximum ratings and characteristics

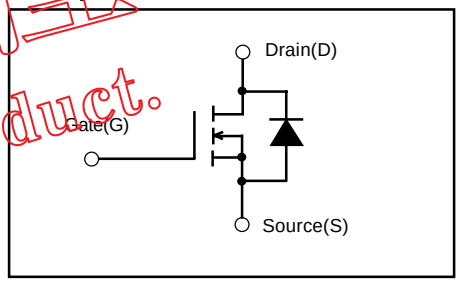
● **Absolute maximum ratings (Tc=25°C unless otherwise specified)**

Item	Symbol	Rating	Unit	Remarks
Drain-source voltage	V_{DS}	60	V	
Continuous drain current	I_D	±100	A	
Pulsed drain current	$I_{D(puls)}$	±400	A	
Gate-source peak voltage	V_{GS}	±20	V	
Maximum avalanche energy	E_{AV}	1268.3	mJ	*1
Maximum power dissipation	P_D	125	W	
Operating and storage temperature range	T_{ch}	+150	°C	
	T_{stg}	-55 to +150	°C	

*1 L=0.169mH, Vcc=24V

廃型機種
Discontinued product.

■ Equivalent circuit schematic



● **Electrical characteristics (T_c =25°C unless otherwise specified)**

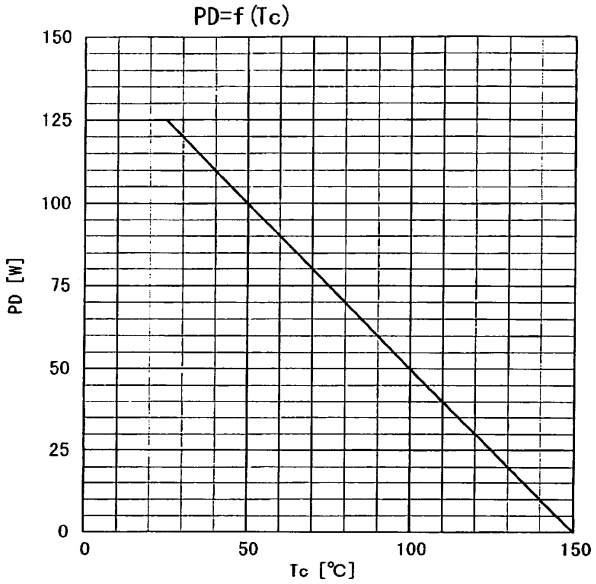
Item	Symbol	Test Conditions		Min.	Typ.	Max.	Units
Drain-source breakdown voltage	$V_{(BR)DSS}$	I_D=1mA V_{GS}=0V		60			V
Gate threshold voltage	$V_{GS(th)}$	I_D=1mA V_{DS}=V_{GS}		1.0	1.5	2.0	V
Zero gate voltage drain current	I_{DSS}	V_{DS}=60V V_{GS}=0V	T_{ch}=25°C		10	500	μA
			T_{ch}=125°C		0.2	1.0	mA
Gate-source leakage current	I_{GSS}	V_{GS}=±20V V_{DS}=0V			10	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	I_D=50A V_{GS}=10V	V_{GS}=4V		7.0	11.0	mΩ
			V_{GS}=10V		5.0	6.5	mΩ
Forward transconductance	g_{fs}	I_D=50A V_{DS}=25V		40	80		S
Input capacitance	C_{iss}	V_{DS}=25V			6700	10050	pF
Output capacitance	C_{oss}	V_{GS}=0V			2100	3150	
Reverse transfer capacitance	C_{rss}	f=1MHz			570	860	
Turn-on time	$t_{d(on)}$	V_{CC}=30V R_G=10 Ω			20	30	ns
	t_r	I_D=100A			160	300	
Turn-off time	$t_{d(off)}$	V_{GS}=10V			410	620	
	t_f				330	500	
Avalanche capability	I_{AV}	L=100μH T_{ch}=25°C		100			A
Diode forward on-voltage	V_{SD}	I_F=100A V_{GS}=0V T_{ch}=25°C			1.0	1.5	V
Reverse recovery time	t_{rr}	I_F=50A			85		ns
Reverse recovery charge	Q_{rr}	-di/dt=100A/μs T_{ch}=25°C			0.21		μC

● **Thermal characteristics**

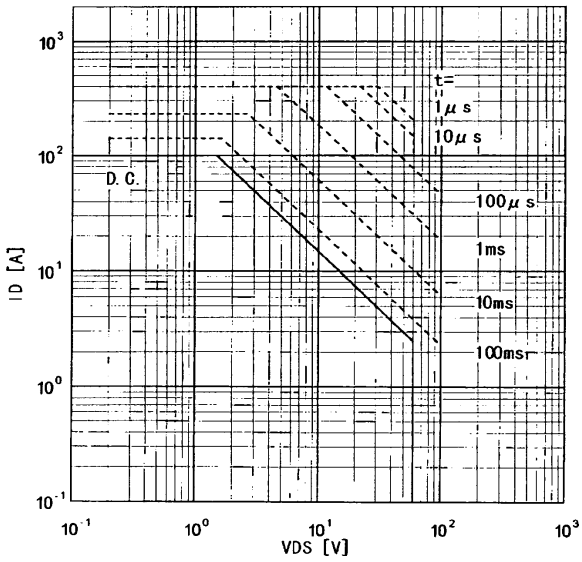
Item	Symbol	Min.	Typ.	Max.	Units
Thermal resistance	$R_{th(ch-c)}$			1.0	°C/W
	$R_{th(ch-a)}$			30.0	°C/W

Characteristics

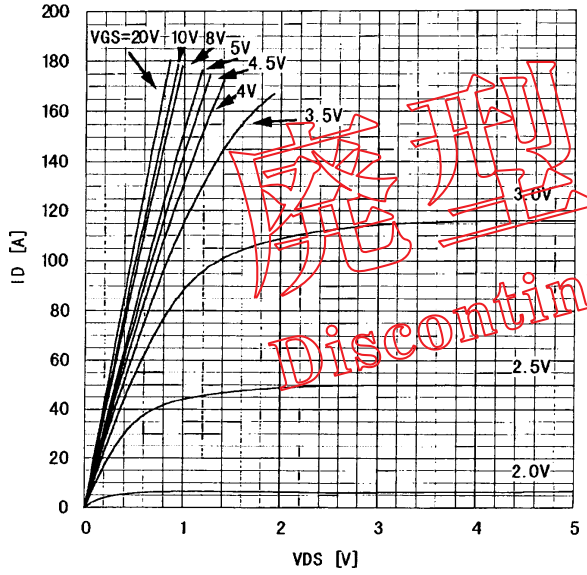
Power Dissipation
PD=f(Tc)



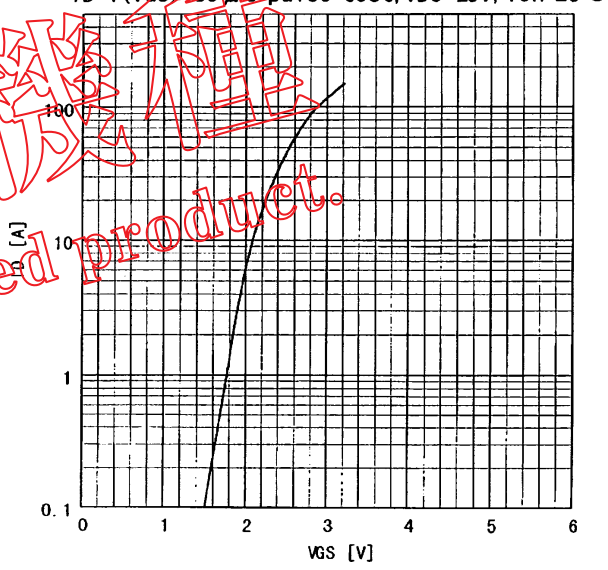
Safe operating area
ID=f(VDS):D=0.01,Tc=25℃



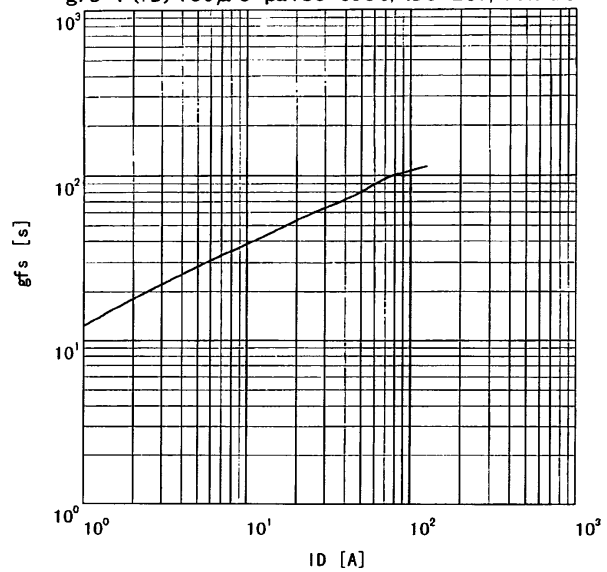
Typical output characteristics
ID=f(VDS):80μs pulse test,Tc=25℃



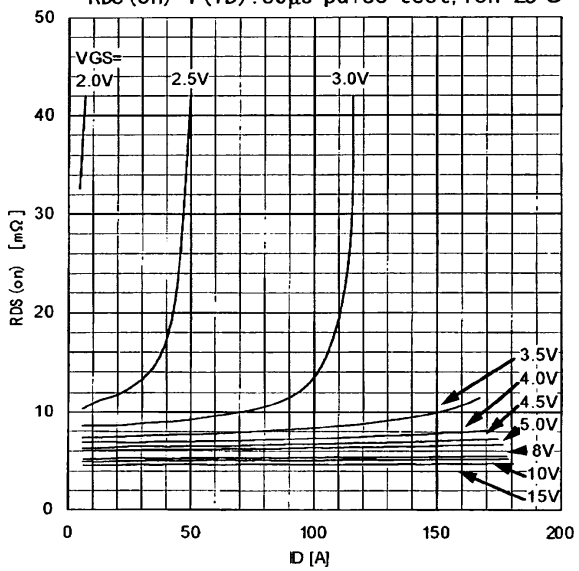
Typical transfer characteristics
ID=f(VGS):80μs pulse test,VDS=25V,Tch=25℃



Typical forward transconductance
gfs=f(ID):80μs pulse test,VDS=25V,Tch=25℃

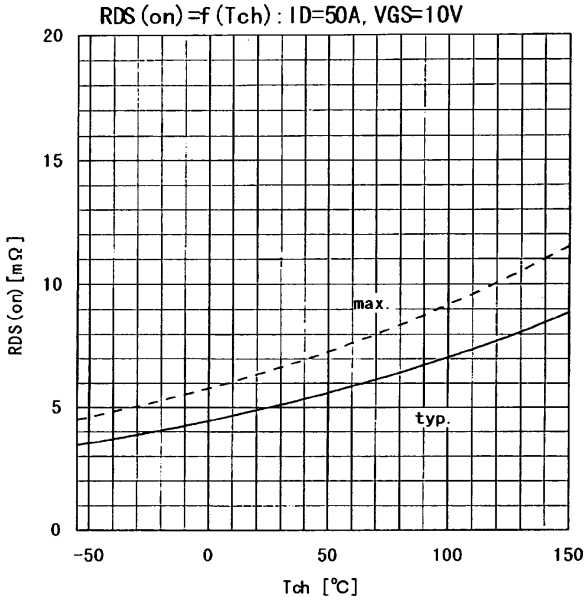


Typical Drain-Source on-State Resistance
RDS(on)=f(ID):80μs pulse test,Tch=25℃

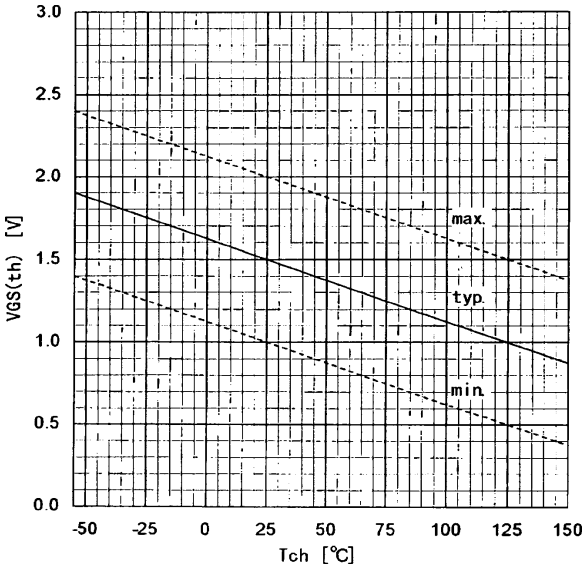


廢止機種
Discontinued product.

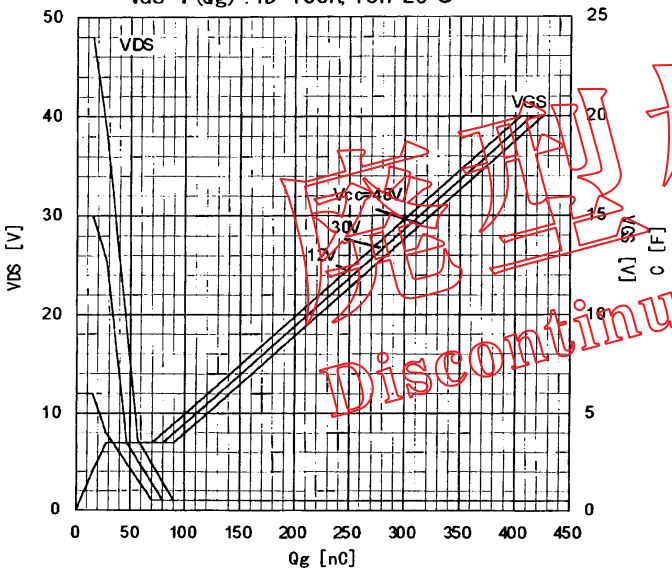
Drain-source on-state resistance
RDS(on)=f(Tch) : ID=50A, VGS=10V



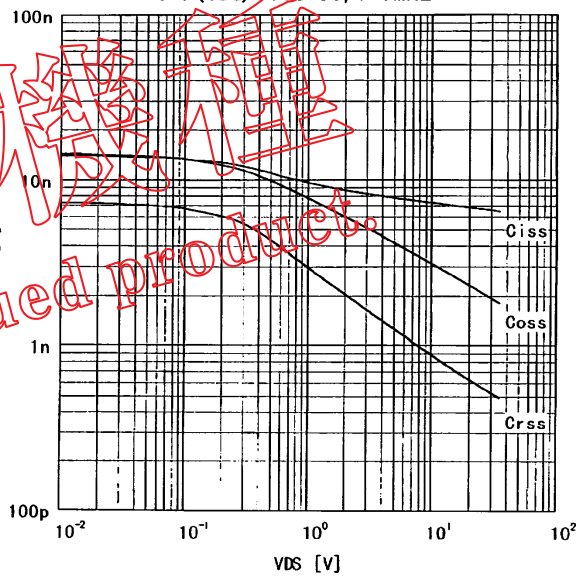
Gate Threshold Voltage vs. Tch
VGS(th)=f(Tch) : VDS=VGS, ID=1mA



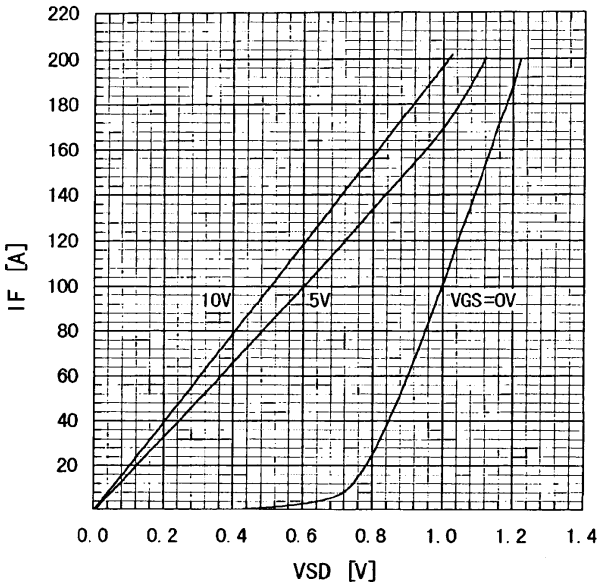
Typical Gate Charge Characteristics
VGS=f(Qg) : ID=100A, Tch=25°C



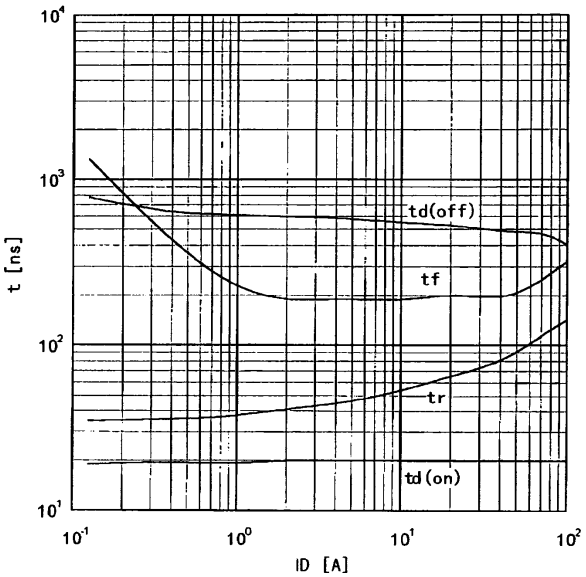
Typical capacitances
C=f(VDS) : VGS=0V, f=1MHz



Typical Forward Characteristics of Reverse Diode
IF=f(VSD) : 80μs pulse test, Tch=25°C



Typical Switching Characteristics vs. ID
t=f(ID) : Vcc=30V, VGS=10V, RG=10Ω



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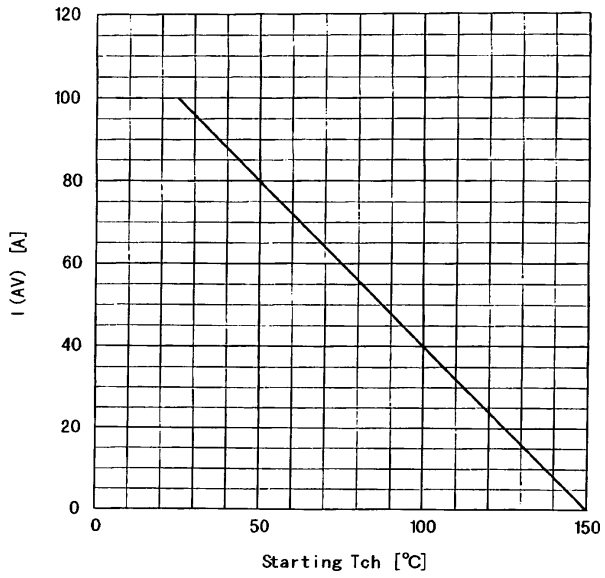
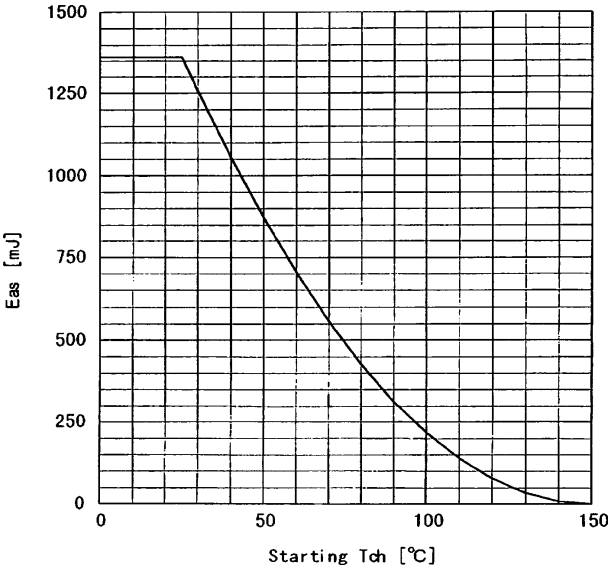
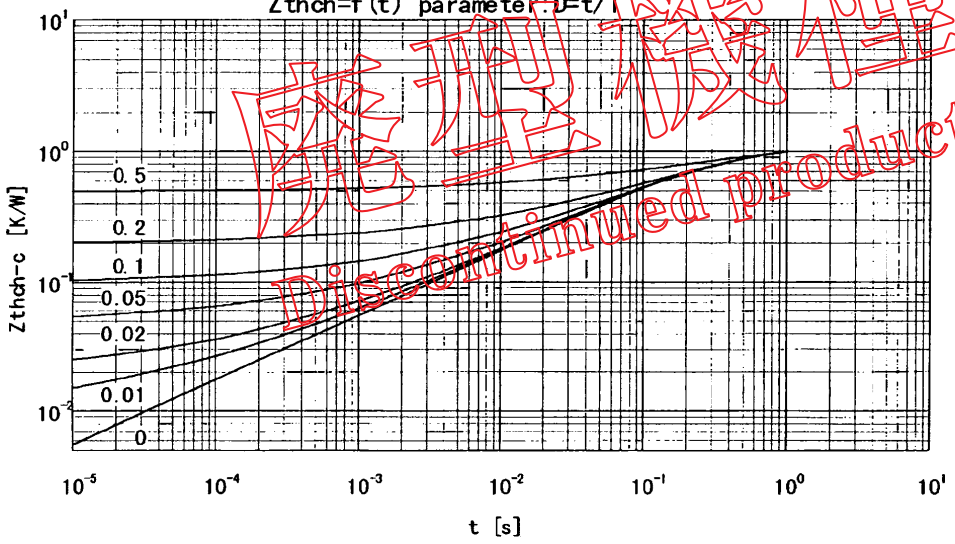
Maximum Avalanche Current vs. starting Tch
I(AV)=f(starting Tch)



Maximum Avalanche energy vs. starting Tch
Eas=f(starting Tch):Vcc=24V, I_{AV}≦100A



Transient thermal impedande
Zthch=f(t) parameter:D=t/T



Discontinued product.